NP501-00026-0v01-E

FRAM
MB85R4M2T

The MB85R4M2T is an FRAM chip consisting of 262,144 words×16 bits of nonvolatile memory cells fabricated using ferroelectric process and CMOS process technologies.
The MB85R4M2T uses a pseudo-SRAM interface that is compatible with conventional asynchronous SRAM.

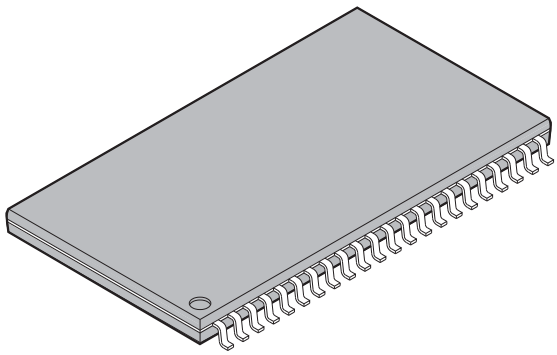
■ FEATURES

- **Bit configuration** : 262,144 words×16 bits
- **LB and UB data byte control** : Available Configuration of 524,288 words × 8 bits
- **Read/write endurance** : 10^{13} times / 16 bits
- **Data retention** : 10 years (+85 °C)
- **Operating power supply voltage** : 1.8V to 3.6V
- **Low power operation** : Operating power supply current 20 mA (Max)
  Standby current 150 µA (Max)
  Sleep current 20 µA (Max)
- **Operation ambient temperature range** : -40 °C to +85 °C
- **Package** : 44-pin plastic TSOP (FPT-44P-M34)
  RoHS compliant

■ ORDERING INFORMATION

Product name	Package	Shipping form
MB85R4M2TFN-G-ASE1	44-pin plastic TSOP (FPT-44P-M34)	Tray

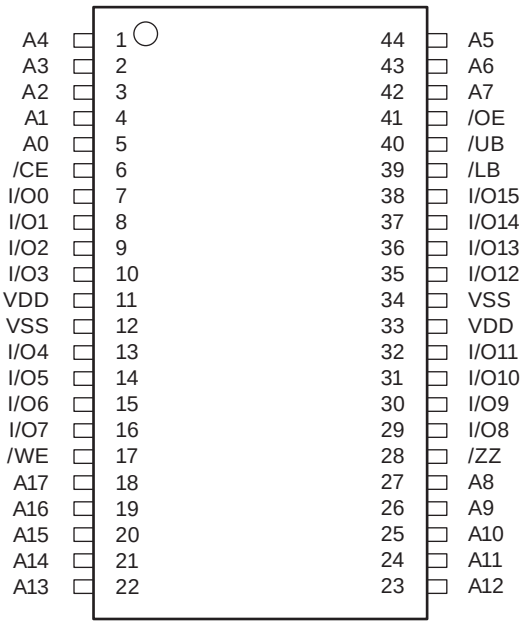
■ OUTLINE OF PACKAGE



Plastic TSOP, 44-pin
(FPT-44P-M34)

■ PIN ASSIGNMENT

(TOP VIEW)



FPT-44P-M34

Pin name	Description
A0 to A17	Address Input pins
I/O0 to I/O15	Data Input / Output pins
/CE	Chip Enable Input pin
/WE	Write Enable Input pin
/OE	Output Enable Input pin
/ZZ	Sleep Mode Input pin
/LB, /UB	Lower/Upper byte Control Input pins
VDD	Supply Voltage pin
VSS	Ground pin

■ BLOCK DIAGRAM